



Product Overview

NTMFS4C06N: Power MOSFET 30V 69A 4 mOhm Single N-Channel S0-8FL

For complete documentation, see the data sheet

Product Description

NTMFS4C06N

Features

- Low RDS(on) to Minimize Conduction Losses
- Low Capacitance to Minimize Driver Losses
- Optimized Gate Charge to Minimize Switching Losses
- These Devices are PbFree and are RoHS Compliant

Applications

- CPU Power Delivery
- DCDC Converters

Part Electrical Specifications

Product	Compliance	Status	Channel Polarity	Configuration	$V_{DS}^{(BR)}$ Min (V)	$V_{GS}^{(max)}$ (V)	$V_{GS}^{(th)}$ (V)	$I_D^{(max)}$ (A)	$P_D^{(max)}$ (W)	$r_{DS(on)}^{(max)}$ @ $V_{GS}=2.5V$ (m)	$r_{DS(on)}^{(max)}$ @ $V_{GS}=4.5V$ (m)	$r_{DS(on)}^{(max)}$ @ $V_{GS}=10V$ (m)	$Q_g^{(Typ)}$ @ $V_{GS}=4.5V$ (nC)	$Q_g^{(Typ)}$ @ $V_{GS}=10V$ (nC)	$Q_{gd}^{(Typ)}$ @ $V_{GS}=4.5V$ (nC)	$Q_{rr}^{(Typ)}$ (nC)	$C_{iss}^{(Typ)}$ (pF)	$C_{oss}^{(Typ)}$ (pF)	$C_{rss}^{(Typ)}$ (pF)	Packaging Type
NTMFS4C06NT1G	Pb-free	Active	N-Channel	Single	30	20	2.1	69	30.5		6	4		26	4	22	1683	841	40	SO-8FL / DF N-5
	Halide free																			

For more information please contact your local sales support at www.onsemi.com

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